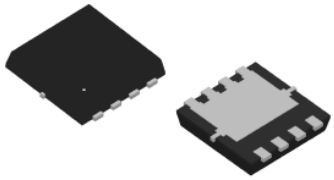
WPM3028B

Single P-Channel, -30V, -36A, Power MOSFET

Http://www.sh-willsemi.com

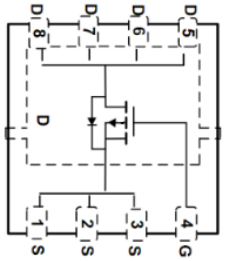
V_{DS} (V)	Typical $R_{DS(on)}$ (mΩ)
-30	8.4 @ V_{GS}=-10V
	15 @ V_{GS}=-4.5V



PDFN3333-8L

Description

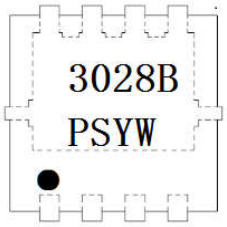
The WPM3028B is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WPM3028B is Pb-free.



Pin configuration (Top view)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance
- Package PDFN3333-8L



3028B = Device Code
PS = Special Code
Y =Year
W = Week (A~z)

Marking

Applications

- DC/DC converters
- Power supply converters circuit
- Load/Power Switching for portable device

Order information

Device	Package	Shipping
WPM3028B-8/TR	PDFN3333-8L	2500/Tape&Reel

Absolute Maximum ratings

Parameter		Symbol	Maximum	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	
Continuous Drain Current [d]	T_C=25°C	I_D	-36	A
	T_C=100°C		-30	A
Pulsed Drain Current [c]		I_{DM}	-93	A
Continuous Drain Current	T_A=25°C	I_{DSM}	-18	A
	T_A=70°C		-14	
Avalanche Energy L=0.3mH [f]		E_{AS}	150	mJ
Power Dissipation [b]	T_C=25°C	P_D	36	W
	T_C=100°C		14	
Power Dissipation [a]	T_A=25°C	P_{DSM}	5.0	W
	T_A=70°C		3.2	
Operating Junction Temperature		T_J	-55 to 150	°C
Storage Temperature Range		T_{STG}	-55 to 150	°C

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance [a]	t ≤ 10 s	$R_{\theta JA}$	20	25	°C/W
	Steady State		48	60	
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	2.8	3.5	

Note:

a The value of $R_{\theta JA}$ is measured with the device mounted on 1-inch^2 (6.45cm^2) with 2oz.(0.071mm thick) Copper pad on a 1.5*1.5 inch^2, 0.06-inch thick FR4 PCB, in a still air environment with T_A =25°C. The power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤10s value and the $T_{J(MAX)}$=150°C. The value in any given application is determined by the user's specific board design.

b The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

c Repetitive rating, ~10us pulse width, duty cycle ~1%, keep initial T_J =25°C, the maximum allowed junction temperature of 150°C.

d The maximum current rating by source bonding technology.

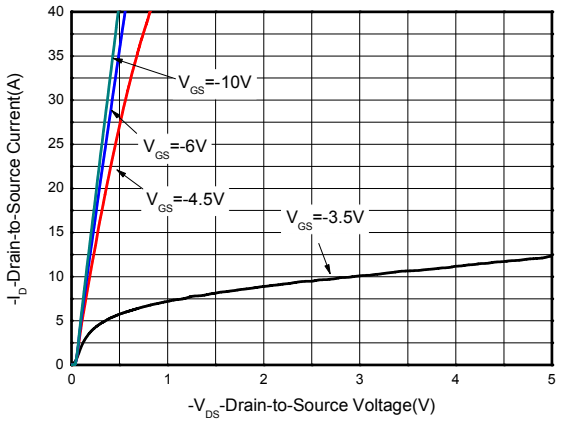
e The static characteristics are obtained using ~380us pulses, duty cycle ~1%.

f L=0.3mH，VDD=-24V，Rg=25Ω，Starting TJ =25°C.

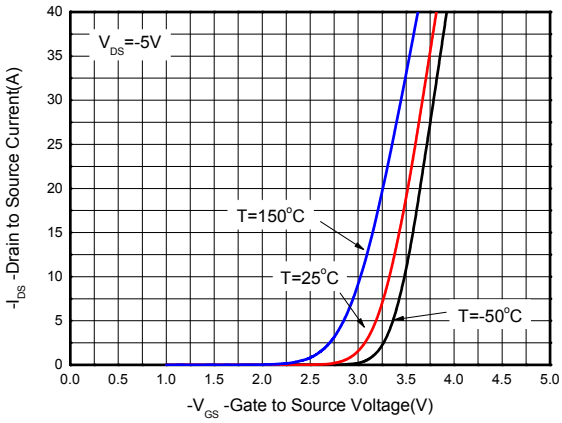
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0 V, I_D = -250uA	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-24V, V_{GS} = 0V			1	uA
Gate-to-source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±25V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = -250uA	-1.0	-2.1	-3.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	V_{GS} =-10V, I_D =-12A		8.4	10.5	mΩ
		V_{GS} =-4.5V, I_D =-8A		15	22.0	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0MHz, V_{DS} = -15 V		1995		pF
Output Capacitance	C_{OSS}			355		
Reverse Transfer Capacitance	C_{RSS}			271		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = -10 V, V_{DS} = -15 V, I_D =-18 A		38.5		nC
Threshold Gate Charge	$Q_{G(TH)}$			4.5		
Gate-to-Source Charge	Q_{GS}			10.5		
Gate-to-Drain Charge	Q_{GD}			7		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V_{GS} = -10 V, V_{DS} = -15 V, R_L=0.83 Ω , R_G=7 Ω		15.8		ns
Rise Time	tr			14		
Turn-Off Delay Time	td(OFF)			65.4		
Fall Time	tf			21.4		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = -1A			1.2	V

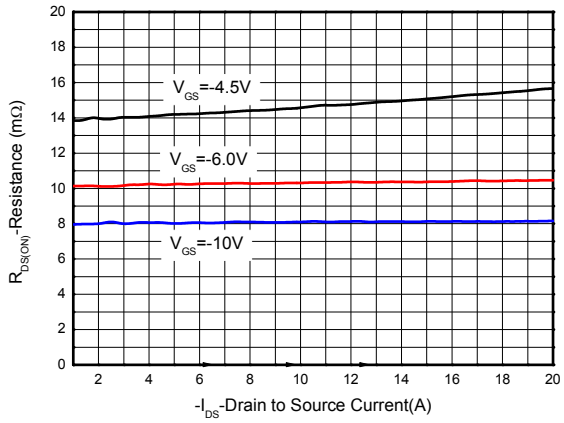
Typical Characteristics (Ta=25°C, unless otherwise noted)



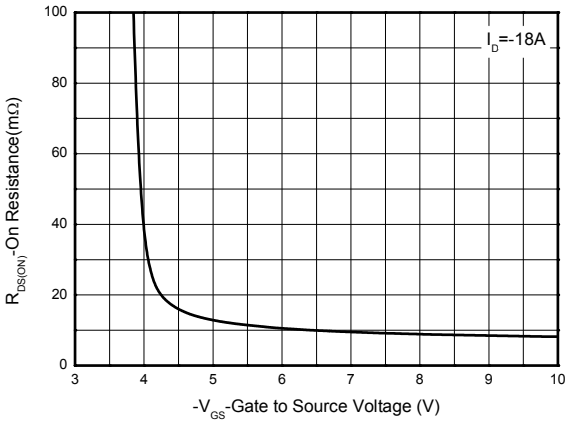
Output Characteristics [e]



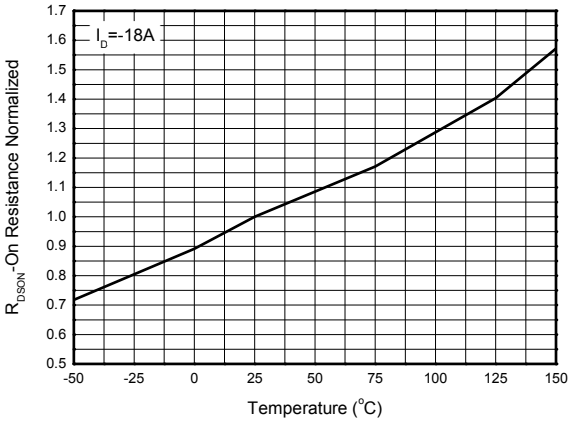
Transfer Characteristics [e]



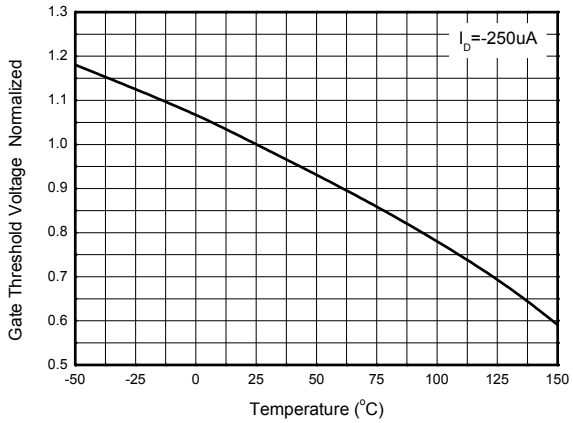
On-Resistance vs. Drain Current [e]



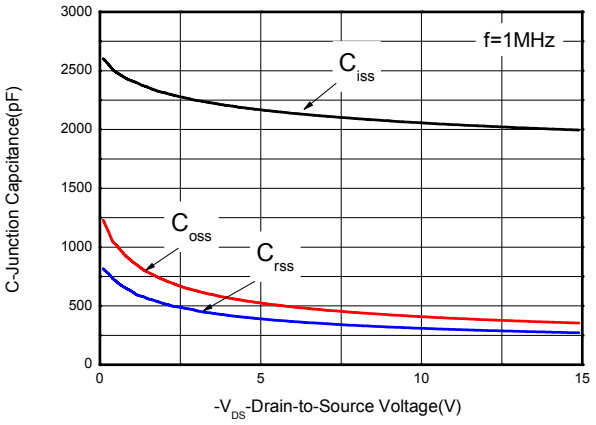
On-Resistance vs. Gate-to-Source Voltage [e]



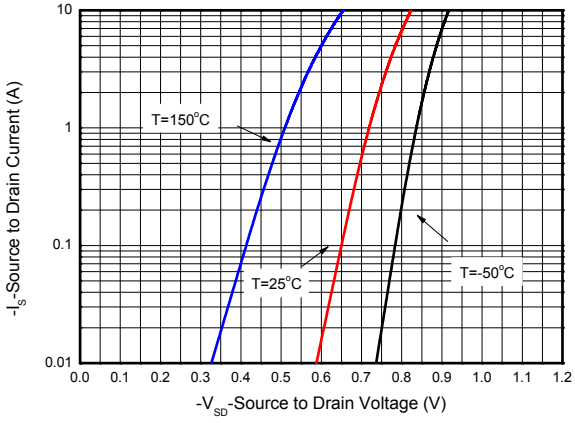
On-Resistance vs. Junction Temperature [e]



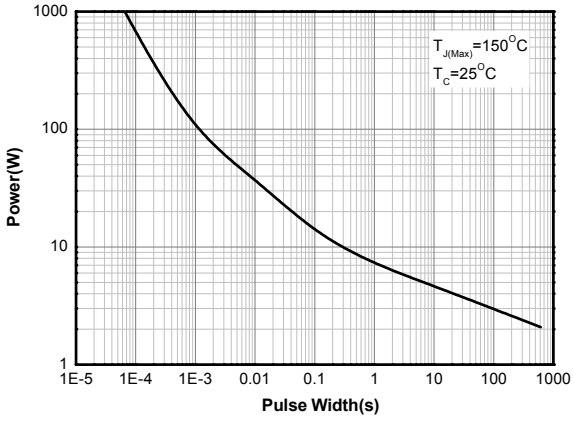
Threshold Voltage vs. Temperature



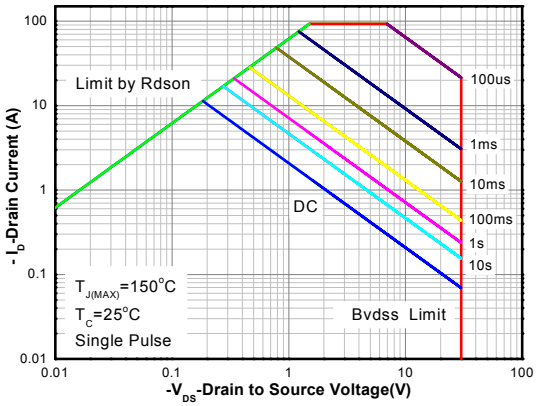
Capacitance



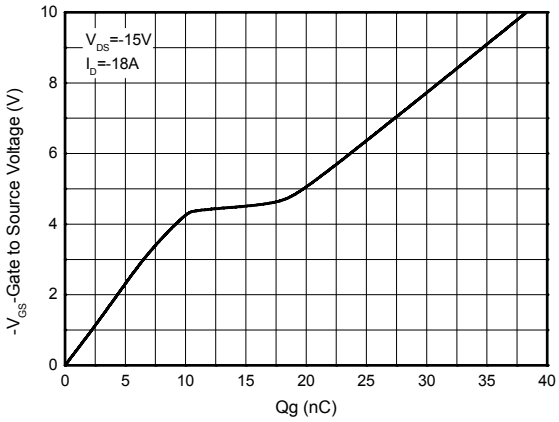
Body Diode Forward Voltage [e]



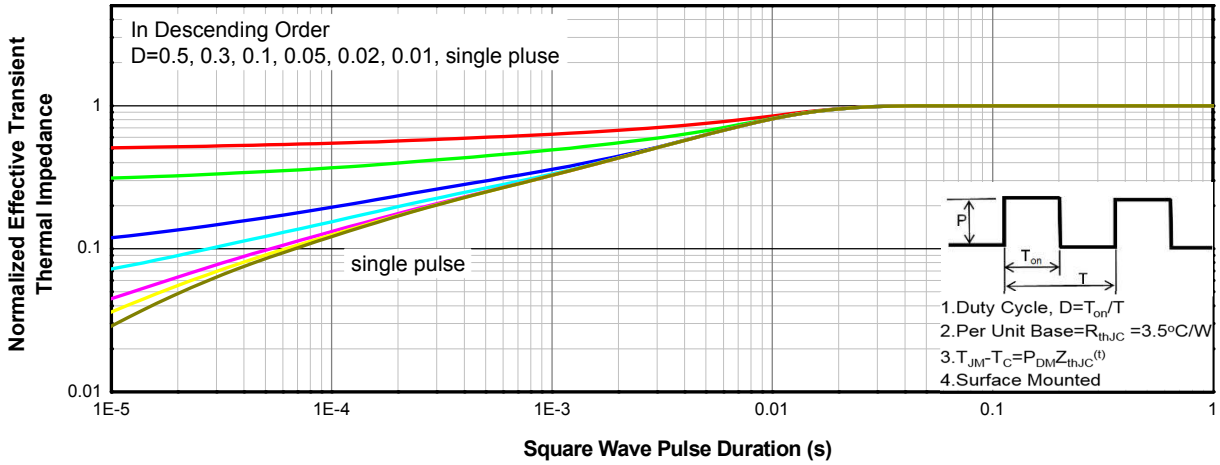
Single Pulse power



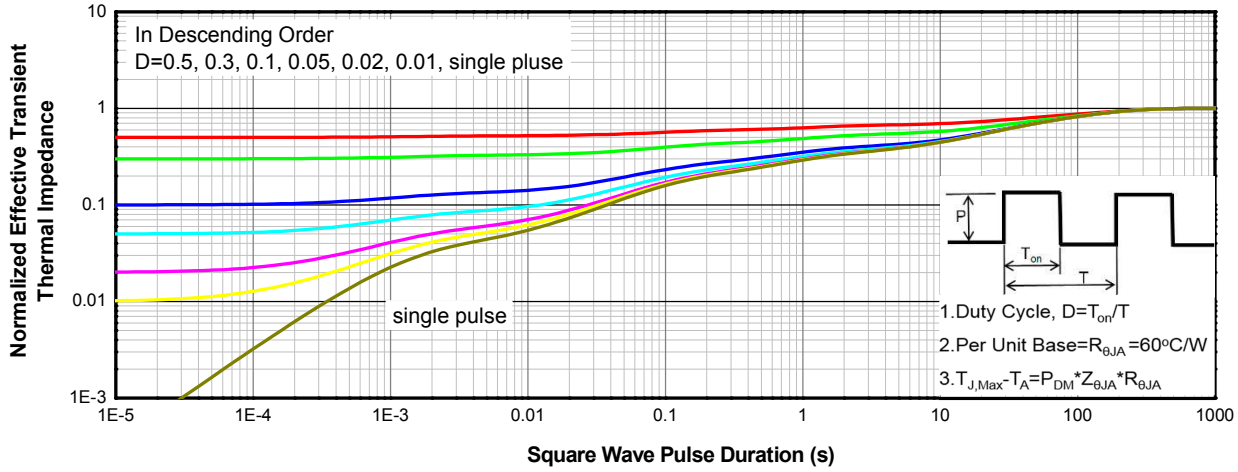
Safe Operating Power



Gate Charge Characteristics



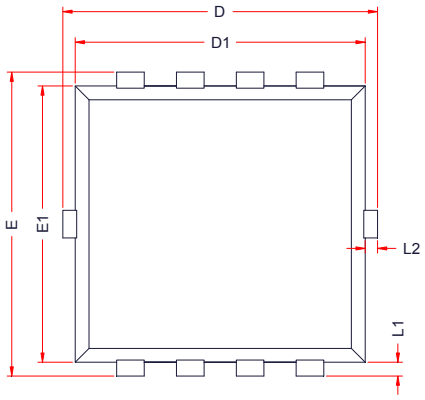
Transient Thermal Response (Junction-to-Case)



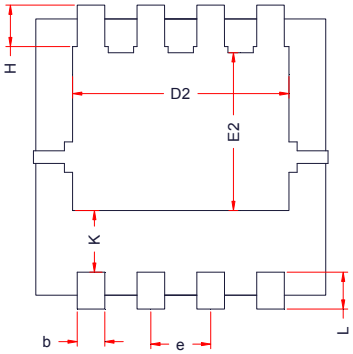
Transient Thermal Response (Junction-to-Ambient)

PACKAGE OUTLINE DIMENSIONS

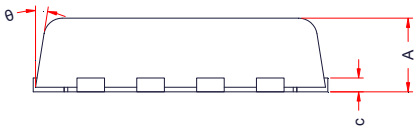
PDFN3333-8L



TOP VIEW



BOTTOM VIEW

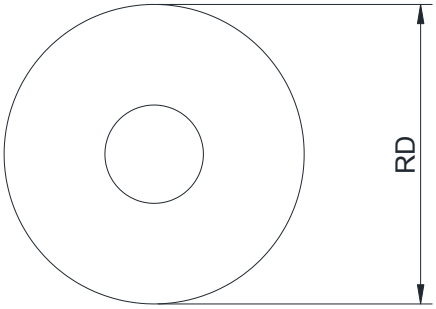


SIDE VIEW

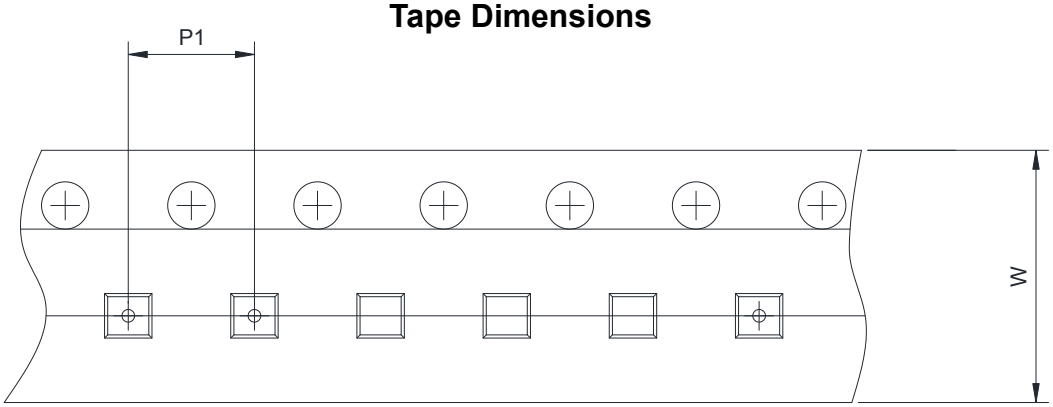
Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.35
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.35	2.45	2.55
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.64	1.74	1.84
H	0.32	0.42	0.52
K	0.59	0.69	0.79
L	0.25	0.40	0.55
L1	0.10	0.15	0.20
L2	-	-	0.15
θ	8°	10°	12°

TAPE AND REEL INFORMATION

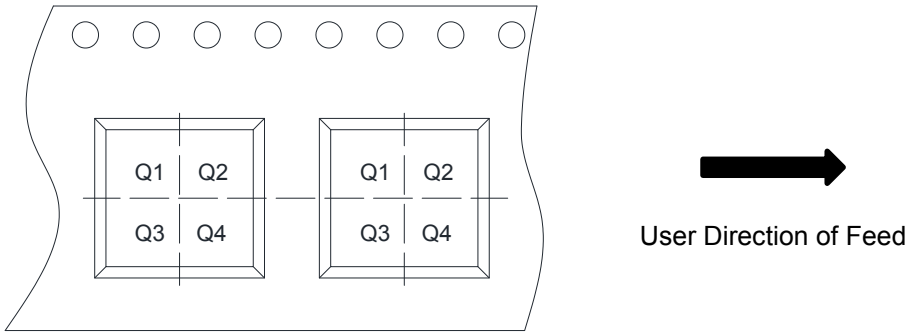
Reel Dimensions



Tape Dimensions



Quadrant Assignments For PIN1 Orientation In Tape



RD	Reel Dimension	☐ 7inch ☑ 13inch
W	Overall width of the carrier tape	☐ 8mm ☑ 12mm ☐ 16mm
P1	Pitch between successive cavity centers	☐ 2mm ☐ 4mm ☑ 8mm
Pin1	Pin1 Quadrant	☑ Q1 ☐ Q2 ☐ Q3 ☐ Q4